

### 1. Global joint venture starts operations as WeEn Semiconductors

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Thank you for your cooperation and understanding,

WeEn Semiconductors



Product data sheet

## 1. General description

Planar passivated sensitive gate four quadrant triac in a SOT404 (D2PAK) plastic package intended for use in general purpose bidirectional switching and phase control applications. This sensitive gate "series E" triac is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

### 2. Features and benefits

- Direct triggering from low power drivers and logic ICs
- High blocking voltage capability
- Low holding current for low current loads and lowest EMI at commutation
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate
- Surface mountable package
- Triggering in all four quadrants

## 3. Applications

- General purpose motor control
- General purpose switching

### 4. Quick reference data

Table 1. Quick reference data

| Symbol              | Parameter                                | Conditions  | Min | Тур | Max | Unit |
|---------------------|--|---|-----|-----|-----|------|
| $V_{DRM}$           | repetitive peak off-<br>state voltage    |   | -   | -   | 800 | V    |
| I <sub>TSM</sub>    | non-repetitive peak on-<br>state current | full sine wave; $T_{j(init)} = 25 \text{ °C}$ ;<br>$t_p = 20 \text{ ms}$ ; Fig. 4; Fig. 5 | -   | -   | 25  | А    |
| I <sub>T(RMS)</sub> | RMS on-state current                     | full sine wave; $T_{mb} \le 107 ^{\circ}\text{C}$ ; Fig. 2; Fig. 3                        | -   | -   | 4   | Α    |
| Static charac       | teristics                                |   |     |     |     |      |
| I <sub>GT</sub>     | gate trigger current                     | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$<br>$T_j = 25 \text{ °C}; Fig. 7$       | -   | 2.5 | 10  | mA   |
|                     |  | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-;$<br>$T_j = 25 \text{ °C}; Fig. 7$       | -   | 4   | 10  | mA   |





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| Symbol         | Parameter       | Conditions  | Min | Тур | Max | Unit |
|----------------|-----------------|---|-----|-----|-----|------|
|                |                 | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2-\text{ G-;}$<br>$T_j = 25 \text{ °C; } Fig. 7$ | -   | 5   | 10  | mA   |
|                |                 | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2-\text{ G+;}$<br>$T_j = 25 \text{ °C; } Fig. 7$ | -   | 11  | 25  | mA   |
| I <sub>H</sub> | holding current | V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>                                  | -   | 2.2 | 15  | mA   |

# 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                    | Simplified outline | Graphic symbol |
|-----|--------|--------------------------------|--------------------|----------------|
| 1   | T1     | main terminal 1                | mb                 | T2—T1          |
| 2   | T2     | main terminal 2                |                    | sym051         |
| 3   | G      | gate                           |                    | ·              |
| mb  | T2     | mounting base; main terminal 2 | D2PAK (SOT404)     |                |

# 6. Ordering information

Table 3. Ordering information

| Type number | Package |  |         |  |  |  |
|-------------|---------|--|---------|--|--|--|
|             | Name    | Description  | Version |  |  |  |
| BT136B-800E | D2PAK   | plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) | SOT404  |  |  |  |

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# 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol              | Parameter                            | Conditions   | Min | Max | Unit             |
|---------------------|--------------------------------------|--|-----|-----|------------------|
| $V_{DRM}$           | repetitive peak off-state voltage    |  | -   | 800 | V                |
| I <sub>T(RMS)</sub> | RMS on-state current                 | full sine wave; $T_{mb} \le 107 \text{ °C}$ ; Fig. 1;<br>Fig. 2; Fig. 3                        | -   | 4   | А                |
| I <sub>TSM</sub>    | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$ ;<br>$t_p = 20 \text{ms}$ ; Fig. 4; Fig. 5 | -   | 25  | Α                |
|                     |                                      | full sine wave; $T_{j(init)} = 25 \text{ °C}$ ;<br>$t_p = 16.7 \text{ ms}$                     | -   | 27  | Α                |
| I <sup>2</sup> t    | I2t for fusing                       | t <sub>p</sub> = 10 ms; SIN  | -   | 3.1 | A <sup>2</sup> s |
| dl <sub>T</sub> /dt | rate of rise of on-state current     | $I_T$ = 6 A; $I_G$ = 0.2 A; $dI_G/dt$ = 0.2 A/ $\mu$ s; T2+ G+                                 | -   | 50  | A/µs             |
|                     |                                      | $I_T = 6 \text{ A}; I_G = 0.2 \text{ A}; dI_G/dt = 0.2 \text{ A}/\mu\text{s};$<br>T2+ G-       | -   | 50  | A/µs             |
|                     |                                      | $I_T = 6 \text{ A}; I_G = 0.2 \text{ A}; dI_G/dt = 0.2 \text{ A}/\mu\text{s};$<br>T2- G-       | -   | 50  | A/µs             |
|                     |                                      | $I_T$ = 6 A; $I_G$ = 0.2 A; $dI_G/dt$ = 0.2 A/ $\mu$ s; T2- G+                                 | -   | 10  | A/µs             |
| I <sub>GM</sub>     | peak gate current                    |  | -   | 2   | Α                |
| P <sub>GM</sub>     | peak gate power                      |  | -   | 5   | W                |
| P <sub>G(AV)</sub>  | average gate power                   | over any 20 ms period  | -   | 0.5 | W                |
| T <sub>stg</sub>    | storage temperature                  |  | -40 | 150 | °C               |
| Tj                  | junction temperature                 |  | -   | 125 | °C               |

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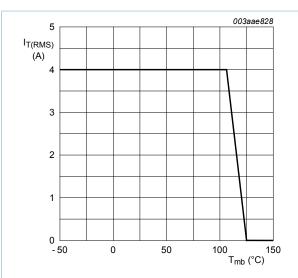
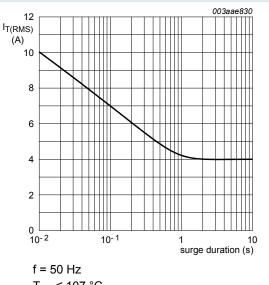
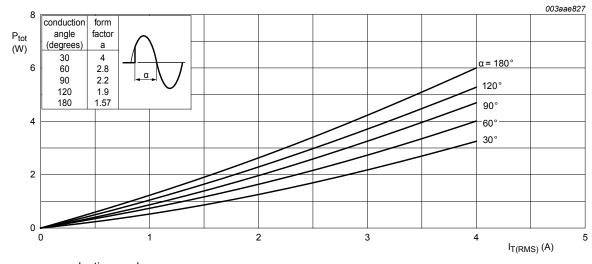


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



 $T_{mb} \le 107 \, ^{\circ}C$ 

Fig. 2. RMS on-state current as a function of surge duration; maximum values



 $\alpha$  = conduction angle

 $a = form factor = I_{T(RMS)} / I_{T(AV)}$ 

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

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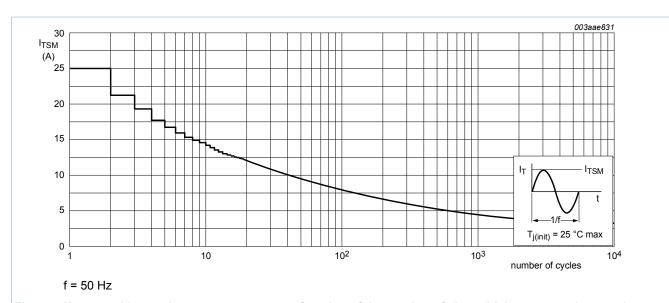
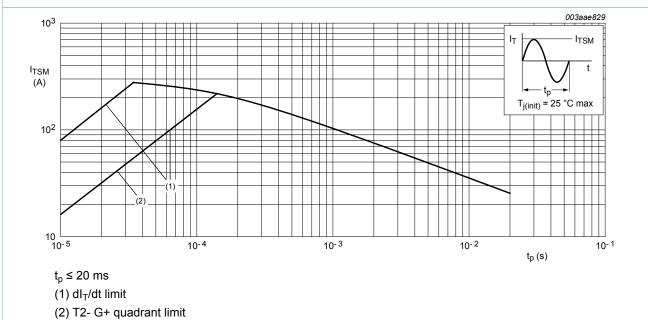


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



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## 8. Thermal characteristics

Table 5. Thermal characteristics

| Symbol                | Parameter   | Conditions                           | Min | Тур | Max | Unit |
|-----------------------|---|--------------------------------------|-----|-----|-----|------|
| R <sub>th(j-mb)</sub> | thermal resistance                                | half cycle; Fig. 6                   | -   | -   | 3.7 | K/W  |
|                       | from junction to mounting base                    | full cycle; Fig. 6                   | -   | -   | 3   | K/W  |
| R <sub>th(j-a)</sub>  | thermal resistance<br>from junction to<br>ambient | PCB (FR4) mounted; minimum pad sizes | -   | 55  | -   | K/W  |

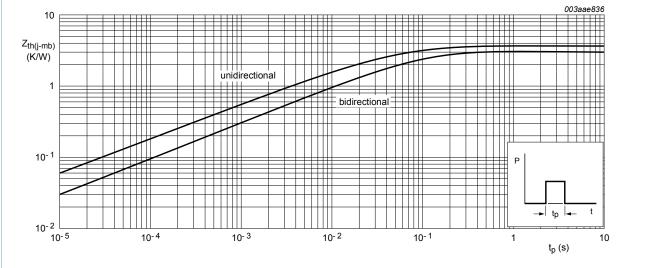


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

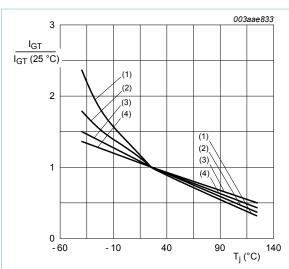
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## 9. Characteristics

Table 6. Characteristics

| Symbol              | Parameter                         | Conditions   | Min      | Тур | Max | Unit |
|---------------------|-----------------------------------|--|----------|-----|-----|------|
| Static char         | racteristics                      |  | '        |     |     |      |
| I <sub>GT</sub>     | gate trigger current              | V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+;<br>T <sub>j</sub> = 25 °C; <u>Fig. 7</u>                      | -        | 2.5 | 10  | mA   |
|                     |                                   | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$<br>$T_j = 25 ^{\circ}\text{C}; Fig. 7$                    | -        | 4   | 10  | mA   |
|                     |                                   | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{ G-};$<br>$T_j = 25 ^{\circ}\text{C}; \underline{\text{Fig. 7}}$ | -        | 5   | 10  | mA   |
|                     |                                   | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G+};$<br>$T_j = 25 ^{\circ}\text{C}; \text{ Fig. 7}$            | -        | 11  | 25  | mA   |
| L                   | latching current                  | V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2+ G+;<br>T <sub>j</sub> = 25 °C; <u>Fig. 8</u>                      | -        | 3   | 15  | mA   |
|                     |                                   | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2+ G-};$<br>$T_j = 25 ^{\circ}\text{C}; \underline{\text{Fig. 8}}$ | -        | 10  | 20  | mA   |
|                     |                                   | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$<br>$T_j = 25 ^{\circ}\text{C}; \underline{\text{Fig. 8}}$ | -        | 2.5 | 15  | mA   |
|                     |                                   | V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2- G+;<br>T <sub>j</sub> = 25 °C; <u>Fig. 8</u>                      | -        | 4   | 20  | mA   |
| Н                   | holding current                   | V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>   | -        | 2.2 | 15  | mA   |
| / <sub>T</sub>      | on-state voltage                  | I <sub>T</sub> = 5 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>   | -        | 1.4 | 1.7 | V    |
| / <sub>GT</sub>     | gate trigger voltage              | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$<br>Fig. 11   | -        | 0.7 | 1   | V    |
|                     |                                   | V <sub>D</sub> = 400 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 125 °C;<br>Fig. 11                                  | 0.25     | 0.4 | -   | V    |
| D                   | off-state current                 | V <sub>D</sub> = 800 V; T <sub>j</sub> = 125 °C  | -        | 0.1 | 0.5 | mA   |
| Dynamic c           | haracteristics                    |  | <u> </u> | -   |     |      |
| dV <sub>D</sub> /dt | rate of rise of off-state voltage | $V_{DM}$ = 536 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit           | -        | 50  | -   | V/µs |
| tgt                 | gate-controlled turn-on time      | $I_{TM}$ = 6 A; $V_D$ = 800 V; $I_G$ = 0.2 A; $dI_G/$ $dt$ = 5 A/ $\mu$ s  | -        | 2   | -   | μs   |

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- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

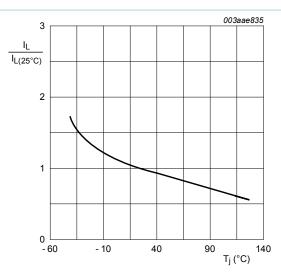


Fig. 8. Normalized latching current as a function of junction temperature

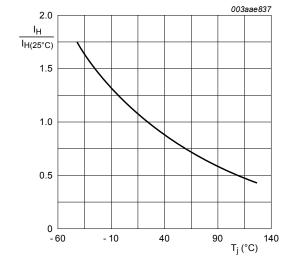
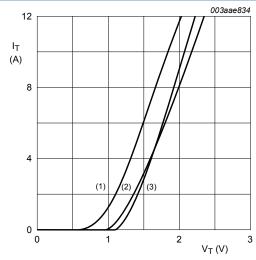


Fig. 9. Normalized holding current as a function of junction temperature



 $V_0 = 1.27 \text{ V}$ 

 $R_s = 0.091 \Omega$ 

(1) T<sub>i</sub> = 125 °C; typical values

(2) T<sub>i</sub> = 125 °C; maximum values

(3)  $T_j = 25$  °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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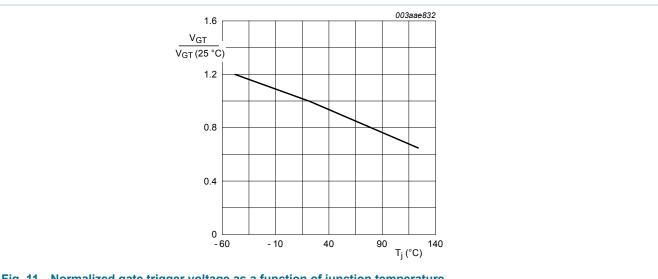
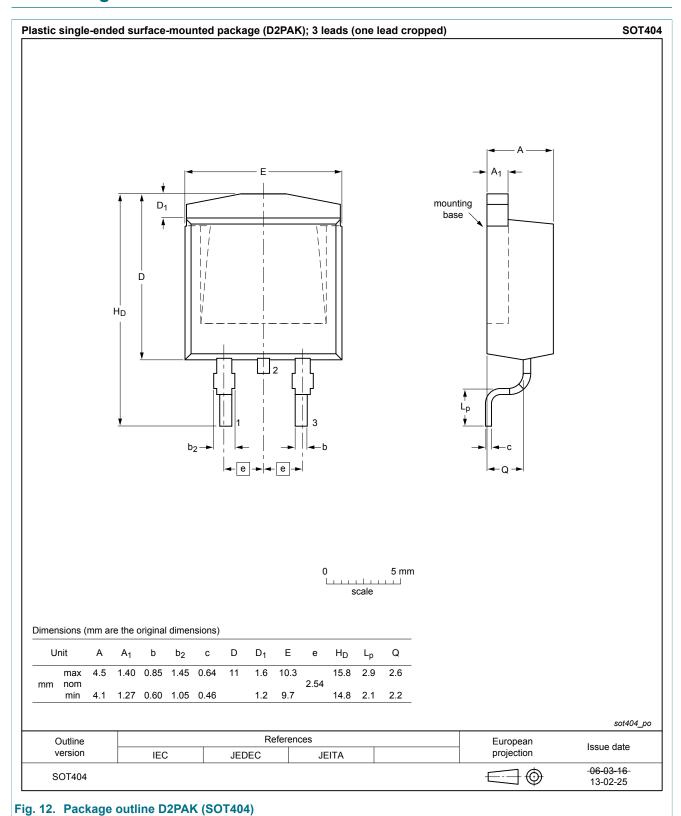


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

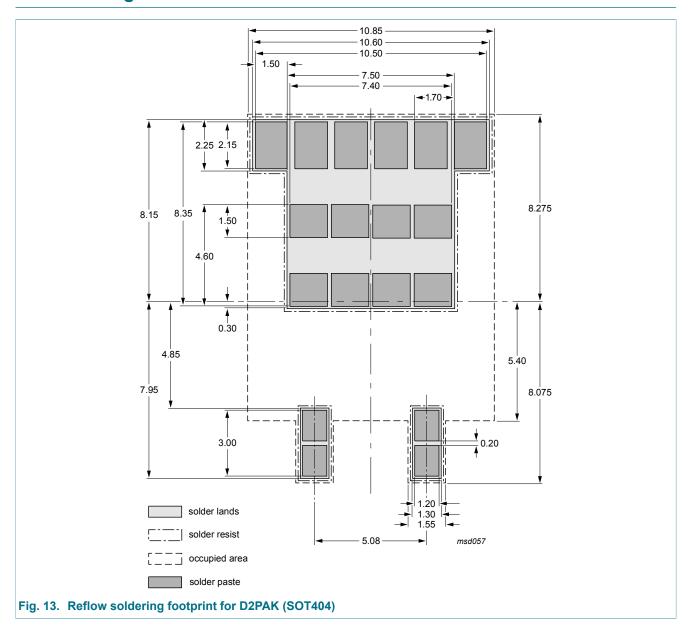
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## 10. Package outline



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# 11. Soldering



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### 12. Legal information

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| Document status [1][2]               | Product status [3] | Definition  |
|--------------------------------------|--------------------|---|
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## BT136B-800E

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